

ANTREX Electronics

Electronic Components Sourcing Information

Product Reference Information

Part Number:	NTNS3A65PZT5G
Manufacturer:	onsemi
Package:	Please confirm with sales
Availability:	Please confirm with sales

Product Page:

<https://antrexco.com/product/details/onsemi/ntns3a65pzt5g.html>

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Contact Information

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WhatsApp: +86-186-8066-5326

Website: <https://antrexco.com>

Quality & Trust

New & Original Components

Supplier verification and packaging condition review

CoC / RoHS / REACH documents available on request

Secure sourcing support for OEM / EMS projects

Note:

This PDF includes an ANTREX product reference cover page.

The original manufacturer datasheet follows from the next page.

NTNS3A65PZ

MOSFET – Single, P-Channel, Small Signal, SOT-883 (XDFN3), 1.0 x 0.6 x 0.4 mm -20 V, -281 mA

Features

- Single P-Channel MOSFET
- Ultra Low Profile SOT-883 (XDFN3) 1.0 x 0.6 x 0.4 mm for Extremely Thin Environments Such as Portable Electronics
- Low $R_{DS(on)}$ Solution in the Ultra Small 1.0 x 0.6 mm Package
- 1.5 V Gate Drive
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

Applications

- High Side Switch
- High Speed Interfacing
- Optimized for Power Management in Ultra Portable Solutions

MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$ unless otherwise stated)

Parameter			Symbol	Value	Unit
Drain-to-Source Voltage			V _{DSS}	−20	V
Gate-to-Source Voltage			V _{GS}	±8	V
Continuous Drain Current (Note 1)	Steady State	T _A = 25°C	I _D	−281	mA
		T _A = 85°C		−202	
	t ≤ 5 s	T _A = 25°C		−332	
Power Dissipation (Note 1)	Steady State	T _A = 25°C	P _D	155	mW
	t ≤ 5 s			218	
Pulsed Drain Current	t _p = 10 μs		I _{DM}	−842	mA
Operating Junction and Storage Temperature			T _J , T _{STG}	−55 to 150	°C
Source Current (Body Diode) (Note 2)			I _S	−130	mA
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)			T _L	260	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. Surface-mounted on FR4 board using the minimum recommended pad size, or 2 mm², 1 oz Cu.
2. Pulse Test: pulse width $\leq 300 \mu\text{s}$, duty cycle $\leq 2\%$

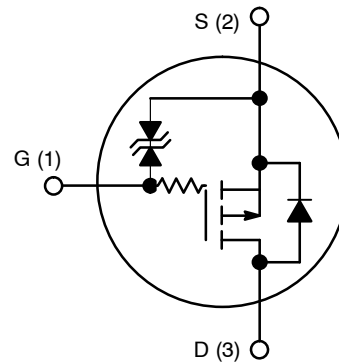


ON Semiconductor®

<http://onsemi.com>

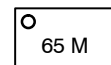
$V_{(BR)DSS}$	$R_{DS(on)}$ MAX	I_D Max
-20 V	1.3 Ω @ -4.5 V	-281 mA
	2.0 Ω @ -2.5 V	
	3.4 Ω @ -1.8 V	
	4.5 Ω @ -1.5 V	

P-CHANNEL MOSFET



SOT-883 (XDFN3)
CASE 506CB

MARKING DIAGRAM



65 = Specific Device Code
M = Date Code

ORDERING INFORMATION

Device	Package	Shipping†
NTNS3A65PZT5G	SOT-883 (Pb-Free)	8000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

NTNS3A65PZ

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Max	Unit
Junction-to-Ambient – Steady State (Note 3)	$R_{\theta JA}$	804	°C/W
Junction-to-Ambient – $t \leq 5$ s (Note 3)	$R_{\theta JA}$	574	

3. Surface-mounted on FR4 board using the minimum recommended pad size, or 2 mm², 1 oz Cu.

ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise stated)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0\text{ V}, I_D = -250\text{ }\mu\text{A}$	-20			V
Drain-to-Source Breakdown Voltage Temperature Coefficient	$V_{(BR)DSS}/T_J$	$I_D = -250\text{ }\mu\text{A}$, ref to 25°C		11		mV/°C
Zero Gate Voltage Drain Current	I_{DSS}	$V_{GS} = 0\text{ V}, V_{DS} = -20\text{ V}$ $T_J = 25^\circ\text{C}$			-1	μA
Gate-to-Source Leakage Current	I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = \pm 5\text{ V}$			± 10	μA

ON CHARACTERISTICS (Note 4)

Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS} = V_{DS}, I_D = -250\text{ }\mu\text{A}$	-0.4		-1.0	V
Negative Threshold Temperature Coefficient	$V_{GS(TH)}/T_J$			2.2		mV/°C
Drain-to-Source On Resistance	$R_{DS(on)}$	$V_{GS} = -4.5\text{ V}, I_D = -200\text{ mA}$		0.9	1.3	Ω
		$V_{GS} = -2.5\text{ V}, I_D = -100\text{ mA}$		1.3	2.0	
		$V_{GS} = -1.8\text{ V}, I_D = -50\text{ mA}$		1.8	3.4	
		$V_{GS} = -1.5\text{ V}, I_D = -10\text{ mA}$		2.3	4.5	Ω
Forward Transconductance	g_{FS}	$V_{DS} = -5\text{ V}, I_D = -200\text{ mA}$		0.58		S
Source-Drain Diode Voltage	V_{SD}	$V_{GS} = 0\text{ V}, I_S = -100\text{ mA}$		-0.8	-1.2	V

CHARGES & CAPACITANCES

Input Capacitance	C_{ISS}	$V_{GS} = 0\text{ V}, \text{freq} = 1\text{ MHz}, V_{DS} = -10\text{ V}$		44		pF
Output Capacitance	C_{OSS}			6.7		
Reverse Transfer Capacitance	C_{RSS}			5.5		
Total Gate Charge	$Q_{G(TOT)}$	$V_{GS} = -4.5\text{ V}, V_{DS} = -10\text{ V}; I_D = -200\text{ mA}$		1.1		nC
Threshold Gate Charge	$Q_{G(TH)}$			0.1		
Gate-to-Source Charge	Q_{GS}			0.2		
Gate-to-Drain Charge	Q_{GD}			0.2		

SWITCHING CHARACTERISTICS, $V_{GS} = 4.5\text{ V}$ (Note 4)

Turn-On Delay Time	$t_{d(ON)}$	$V_{GS} = -4.5\text{ V}, V_{DD} = -10\text{ V}, I_D = -200\text{ mA}, R_G = 2\text{ }\Omega$		18		ns
Rise Time	t_r			32		
Turn-Off Delay Time	$t_{d(OFF)}$			178		
Fall Time	t_f			84		

4. Switching characteristics are independent of operating junction temperatures

TYPICAL CHARACTERISTICS

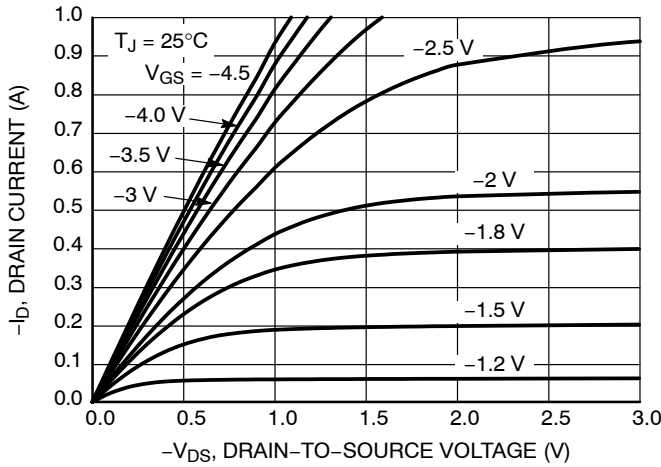


Figure 1. On-Region Characteristics

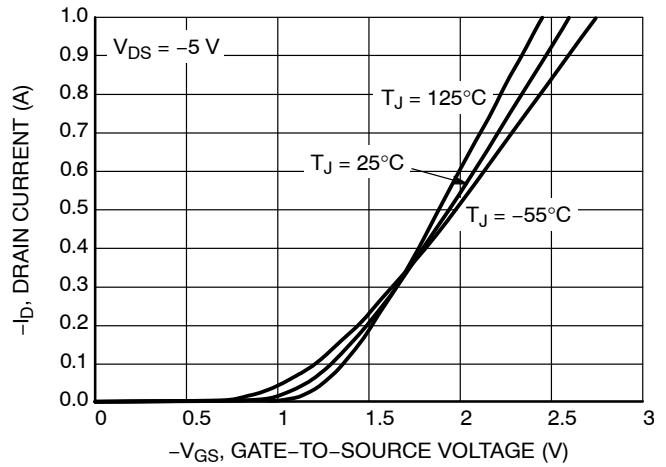


Figure 2. Transfer Characteristics

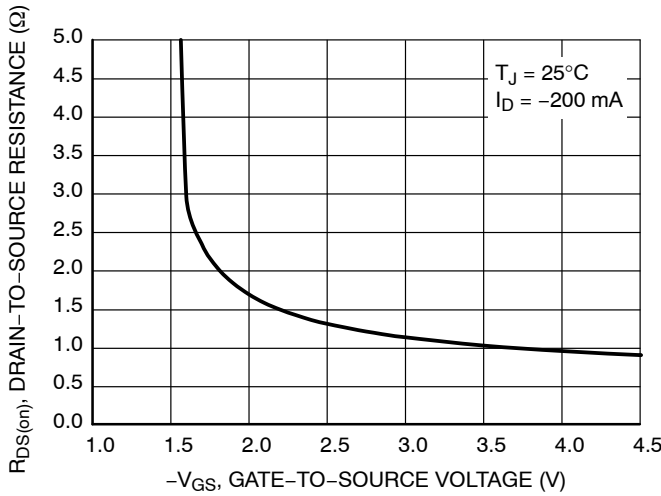


Figure 3. On-Resistance vs. Gate Voltage

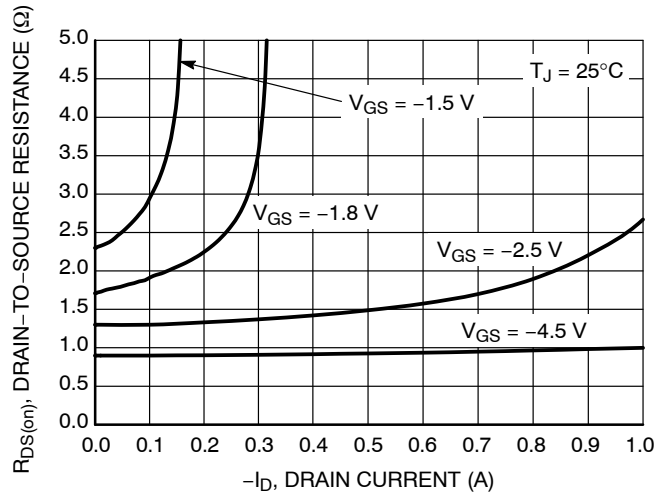


Figure 4. On-Resistance vs. Drain Current and Gate Voltage

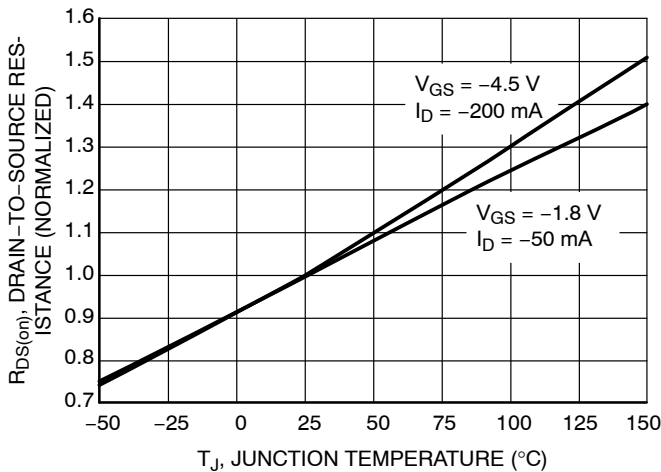


Figure 5. On-Resistance Variation with Temperature

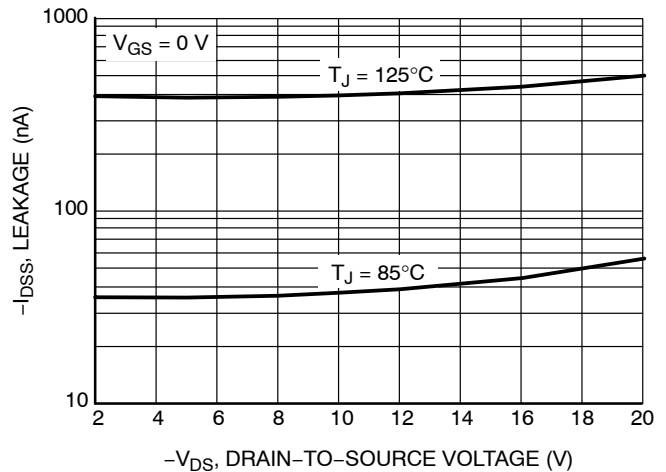


Figure 6. Drain-to-Source Leakage Current vs. Voltage

TYPICAL CHARACTERISTICS

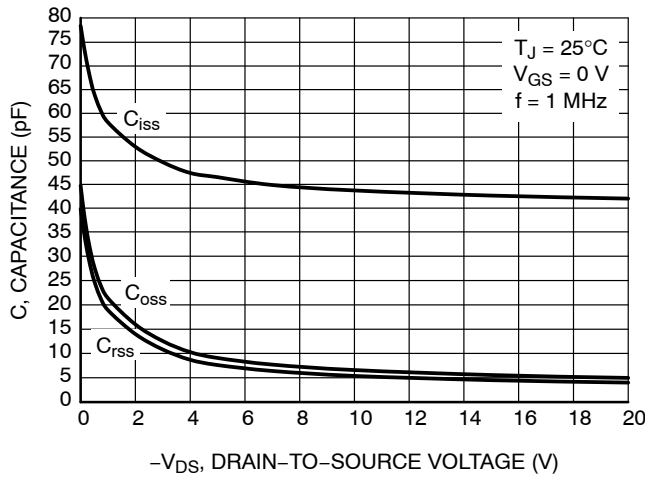


Figure 7. Capacitance Variation

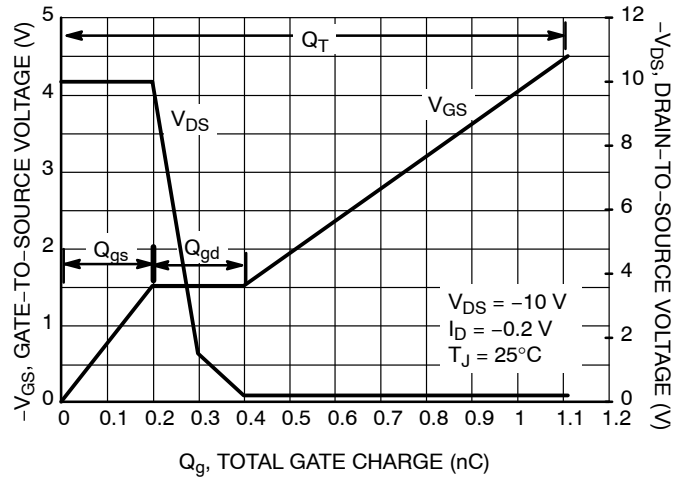


Figure 8. Gate-to-Source Voltage vs. Total Gate Charge

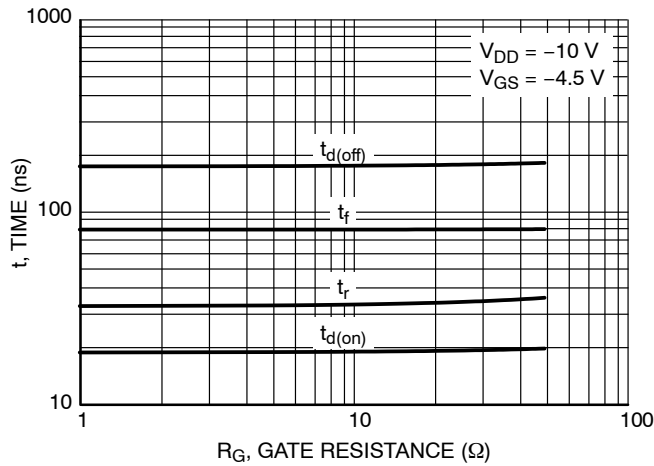


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

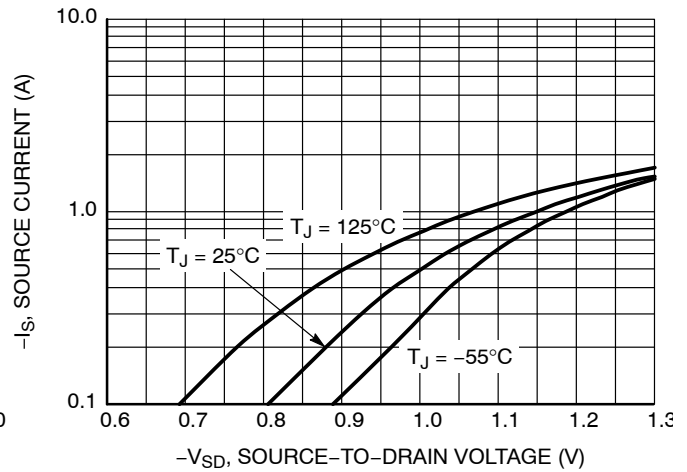


Figure 10. Diode Forward Voltage vs. Current

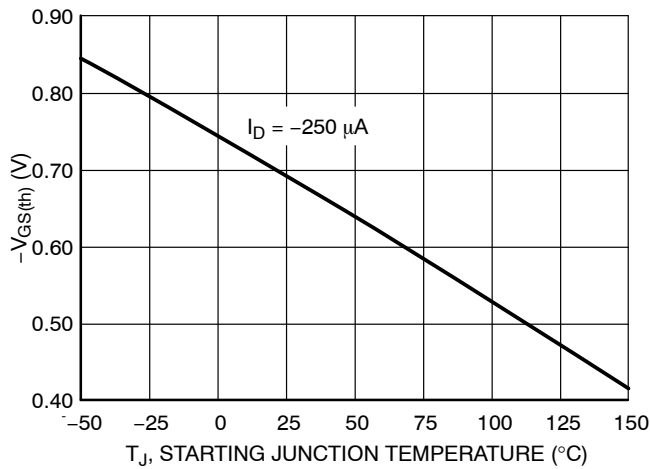


Figure 11. Threshold Voltage

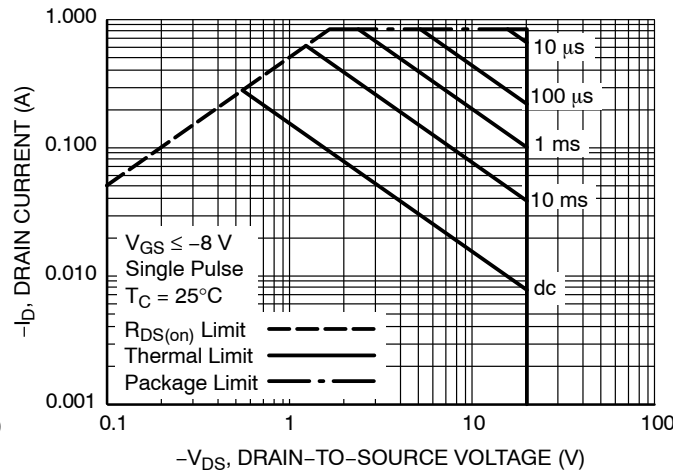


Figure 12. Maximum Rated Forward Biased Safe Operating Area

NTNS3A65PZ

TYPICAL CHARACTERISTICS

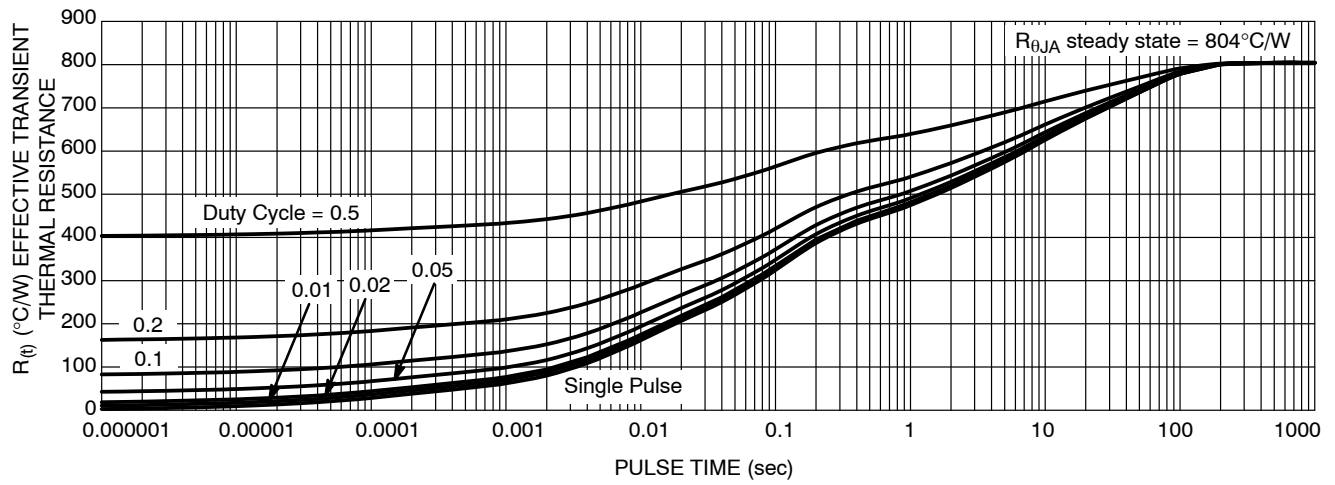
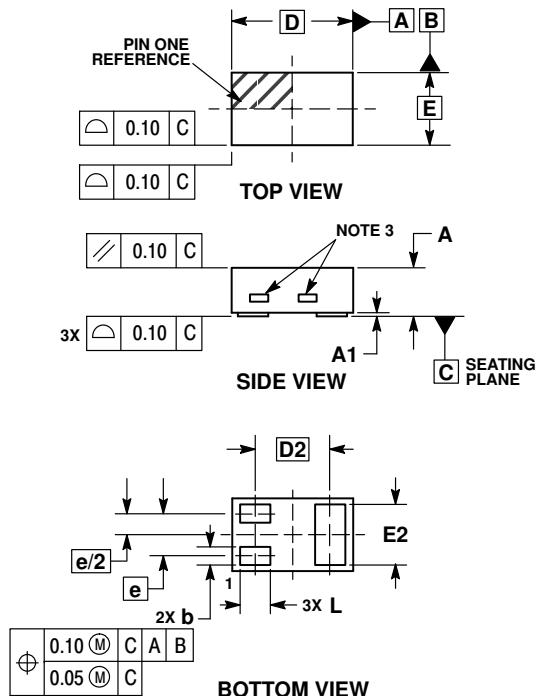


Figure 13. Thermal Response


SOT-883 (XDFN3), 1.0x0.6, 0.35P
CASE 506CB
ISSUE A

DATE 30 MAR 2012

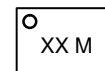
SCALE 8:1



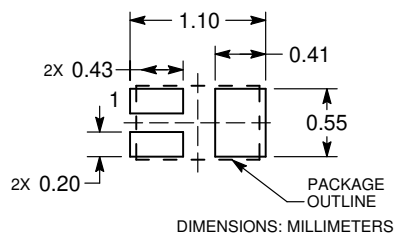
NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. EXPOSED COPPER ALLOWED AS SHOWN.

MILLIMETERS		
DIM	MIN	MAX
A	0.340	0.440
A1	0.000	0.030
b	0.075	0.200
D	0.950	1.075
D2	0.620 BSC	
e	0.350 BSC	
E	0.550	0.675
E2	0.425	0.550
L	0.170	0.300

GENERIC MARKING DIAGRAM*

XX = Specific Device Code
M = Date Code

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G", may or not be present.

RECOMMENDED SOLDER FOOTPRINT*


*For additional information on our Pb-Free strategy and soldering details, please download the onsemi Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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